

X and Ku-Band Internally Matched GaAs Devices

Typical Specifications @ Tc = 25°C

Part Number	Frequency Range (GHz)	Power & Gain					Linearity					Fax on Demand Document Number
		P _{1dB} (dBm)	Linear Gain (dB)	Power Added Efficiency ¹ (%)	V _{DS} (V)	I _{DS} ¹ (A)	IM ₃ (dBc)	P _{out} SCL ² (dBm)	V _{DS} (V)	I _{DSQ} (A)	Package Style	
NEW NEZ1414-2E	14 to 14.5	34.0	7.5	27	9.0	0.9	-45	23	9.0	0.5 x I _{DS}	X-17	217
NEW NEZ1414-4E	14 to 14.5	36.5 ³	7.0	25	9.0	1.8	-45	26 ³	9.0	0.5 x I _{DS}	X-17	233
NEW NEZ1414-8E	14 to 14.5	39.5 ³	6.5	23 ³	9.0	3.5	-45	29 ³	9.0	0.5 x I _{DS}	T-61	230
NEW NEZ1011-2E	10.7 to 11.7	34.0 ³	8.5	35 ³	9.0	0.9	-45	23 ³	9.0	0.5 x I _{DS}	X-17	228
NEW NEZ1011-8E	10.7 to 11.7	39.5 ³	7.5	31 ³	9.0	3.5	-45	29 ³	9.0	0.5 x I _{DS}	T-61	229

- Notes: 1. Measured at P_{1dB}.
 2. SCL = Single Carrier Level
 3. These specs are under negotiation.

GaAs Driver Devices

Typical Specifications @ Tc = 25°C

Part Number	Frequency Range (GHz)	Power & Gain					Linearity (Estimated)				Package Style	Fax on Demand Document Number
		P _{1dB} (dBm)	Gain (dB)	Linear Efficiency ² (%)	Power Added Frequency (GHz)	Test V _{DS} (V)	I _{DS} ² (mA)	IM ₃ (dBc)	P _{out} SCL ³ (dBm)			
CHIP DEVICES												
NE8500100 ⁴	2 to 10	29.5	9.0	39	7.2	10.0	200	-45	19.5	Chip	209	
NE8500200 ¹	2 to 10	34.0	9.0	35	8.5	10.0	—	-45	23.5	Chip	210	
NE900000	1.0 to 18	20.0	9.0	27	14.5	8.0	50	-45	10.0	Chip	212	
NE900100	1.0 to 18	23.0	8.0	27	14.5	8.0	90	-45	13.0	Chip	212	
NE900200	1.0 to 18	25.0	8.0	26	14.5	8.0	180	-45	15.0	Chip	212	
NE1280100 ¹	18 to 40	21.5	10.5	23	18.7	5.0	65	—	—	Chip	204	
NE1280200 ¹	18 to 35	24.5	10.0	20	18.7	5.0	133	—	—	Chip	204	
NE1280400 ¹	18 to 30	27.5	9.0	16	18.7	5.0	340	—	—	Chip	204	
PACKAGED DEVICES												
NEW NE6500278	0.8 to 3.5	33.5	10.0	50	1.96	6.0	500	-45	20.0 ⁵	78		
NEW NE6500496	0.8 to 4.0	36.0	11.5	45	2.3	10.0	400	-45	26.0	96	205	
NEW NE6501077	0.8 to 4.0	39.5	10.5	40	2.3	10.0	1000	-45	29.0	77	207	
NEW NE850R599	0.5 to 10	26.5	9.5	40	7.2	10.0	100	-45	16.5	99	211	
NE8500199	0.5 to 10	29.5	9.0	39	7.2	10.0	200	-45	19.5	99	209	
NEW NE8500295-4	3.5 to 5.5	34.0	12.0	40	4.2	10.0	—	-45	23.5	95	210	
NEW NE8500295-6	5.5 to 7.5	34.0	10.5	37	6.5	10.0	—	-45	23.5	95	210	
NEW NE8500295-8	7.0 to 9.0	34.0	9.0	35	8.5	10.0	—	-45	23.5	95	210	
NE900075	0.5 to 18	20.0	9.0	27	14.5	8.0	50	-45	10.0	75	212	
NE900089A	0.5 to 15	20.5	10.0	27	8.0	8.0	50	-45	10.0	89A	212	
NE900175	0.5 to 18	23.0	8.0	27	14.5	8.0	90	-45	13.0	75	212	
NE900275	0.5 to 18	25.0	8.0	26	14.5	8.0	180	-45	15.0	75	212	
NE900474-13	9.0 to 13.5	31.0	7.0	26	13.5	8.0	450	-45	21.0	74	214	
NE900474-15	13 to 15.2	31.0	7.0	24	15.2	8.0	450	-45	21.0	74	214	

- Notes: 1. Chip has source grounding either by wrap-around metallization or by via holes.
 2. Measured at P_{1dB}.
 3. SCL = Single Carrier Level.
 4. User may bond only one cell for 1/2 W performance.
 5. These specs are under negotiation.